1-Ω DUAL SPDT ANALOG SWITCH 5-V/3.3-V 2-CHANNEL 2:1 MULTIPLEXER/DEMULTIPLEXER

Check for Samples: TS5A23159

FEATURES

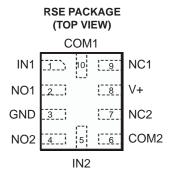
- Isolation in Power-Down Mode, V₊ = 0
- Specified Break-Before-Make Switching
- Low ON-State Resistance (1 Ω)
- Control Inputs Are 5.5-V Tolerant
- Low Charge Injection
- Excellent ON-State Resistance Matching
- Low Total Harmonic Distortion (THD)
- 1.65-V to 5.5-V Single-Supply Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 2000-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)

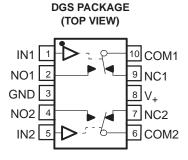
APPLICATIONS

- Cell Phones
- PDAs
- Portable Instrumentation
- Audio and Video Signal Routing
- Low-Voltage Data-Acquisition Systems
- Communication Circuits
- Modems
- Hard Drives
- Computer Peripherals
- · Wireless Terminals and Peripherals

DESCRIPTION

The TS5A23159 is a dual single-pole double-throw (SPDT) analog switch that is designed to operate from 1.65 V to 5.5 V. The device offers low ON-state resistance and excellent ON-state resistance matching with the break-before-make feature, to prevent signal distortion during the transferring of a signal from one channel to another. The device has an excellent total harmonic distortion (THD) performance and consumes very low power. These features make this device suitable for portable audio applications.







Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



SUMMARY OF CHARACTERISTICS(1)

Configuration	Dual 2:1 Multiplexer/Demultiplexer (2 × SPDT)
Number of channels	2
ON-state resistance (r _{on})	1.1 Ω
ON-state resistance match (Δr _{on})	0.1 Ω
ON-state resistance flatness (r _{on(flat)})	0.15 Ω
Turn-on/turn-off time (t _{ON} /t _{OFF})	20 ns/15 ns
Break-before-make time (t _{BBM})	12 ns
Charge injection (Q _C)	–7 pC
Bandwidth (BW)	100 MHz
OFF isolation (O _{ISO})	-65 dB at 1 MHz
Crosstalk (X _{TALK})	-66 dB at 1 MHz
Total harmonic distortion (THD)	0.01%
Leakage current (I _{NO(OFF)} /I _{NC(OFF)})	±20 nA
Power-supply current (I+)	50 nA
Package options	10-pin VSSOP and UQFN

(1) $V_+ = 5 \text{ V}, T_A = 25^{\circ}\text{C}$

FUNCTION TABLE

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
Н	OFF	ON

Absolute Minimum and Maximum Ratings⁽¹⁾ (2)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V ₊	Supply voltage range ⁽³⁾		-0.5	6.5	V
$\begin{matrix} V_{NC} \\ V_{NO} \\ V_{COM} \end{matrix}$	Analog voltage range ⁽³⁾ (4) (5)		-0.5	V ₊ + 0.5	V
I _K	Analog port diode current	V_{NC} , V_{NO} , $V_{COM} < 0$	-50		mA
I _{NC}	On-state switch current		-200	200	
I _{NO} I _{COM}	On-state peak switch current (6)	V_{NC} , V_{NO} , $V_{COM} = 0$ to V_{+}	-400	400	mA
V_{I}	Digital input voltage range (3) (4)		-0.5	6.5	V
I_{IK}	Digital input clamp current	V _I < 0	-50		mA
I ₊	Continuous current through V ₊			100	mA
I _{GND}	Continuous current through GND		-100	100	mA
0	Deales as the second income days as (7)	DGS package		165	9 0 // //
θ_{JA}	Package thermal impedance ⁽⁷⁾	RSE package		TBD	°C/W
T _{stg}	Storage temperature range		-65	150	°C

⁽¹⁾ Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

Product Folder Links: TS5A23159

⁽²⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

³⁾ All voltages are with respect to ground, unless otherwise specified.

⁽⁴⁾ The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

⁽⁵⁾ This value is limited to 5.5 V maximum.

⁶⁾ Pulse at 1-ms duration < 10% duty cycle

⁽⁷⁾ The package thermal impedance is calculated in accordance with JESD 51-7.



Electrical Characteristics for 5-V Supply⁽¹⁾

 $V_{+} = 4.5 \text{ V}$ to 5.5 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CON	DITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch								,	
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V ₊	V
Peak ON	r _{peak}	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON,	25°C	4.5 V		8.0	1.1	Ω
resistance	F-5	$I_{COM} = -100 \text{ mA},$	See Figure 14	Full				1.5	
ON-state	r _{on}	V_{NO} or $V_{NC} = 2.5 \text{ V}$,	Switch ON,	25°C	4.5 V		0.7	0.9	Ω
resistance	011	$I_{COM} = -100 \text{ mA},$	See Figure 14	Full				1.1	
ON-state resistance match between channels	Δr _{on}	V_{NO} or V_{NC} = 2.5 V, I_{COM} = -100 mA,	Switch ON, See Figure 14	25°C Full	4.5 V		0.05	0.1	Ω
ON-state		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 14	25°C			0.15		
resistance	r _{on(flat)}	V_{NO} or $V_{NC} = 1 \text{ V}, 1.5 \text{ V},$	Switch ON,	25°C	4.5 V		0.1	0.25	Ω
flatness		$I_{COM} = -100 \text{ mA},$	See Figure 14	Full				0.25	
		V_{NC} or $V_{NO} = 1 \text{ V}$,		25°C		-20	2	20	
NC, NO OFF leakage current	I _{NO(OFF)} , I _{NC(OFF)}	$V_{COM} = 1 \text{ V to } 4.5 \text{ V,}$ or $V_{NC} \text{ or } V_{NO} = 4.5 \text{ V,}$ $V_{COM} = 1 \text{ V to } 4.5 \text{ V,}$	Switch OFF, See Figure 15	Full	5.5 V	-100		100	nA
Carront	I _{NC(PWROFF)} ,	V_{NC} or $V_{NO} = 0$ to 5.5 V,	Switch OFF,	25°C	0 V	-1	0.2	1	
	I _{NO(PWROFF)}	$V_{COM} = 5.5 \text{ V to } 0,$	See Figure 15	Full	0 0	-20		20	μA
		V_{NC} or $V_{NO} = 1 V$,		25°C		-20	2	20	
NC, NO ON leakage current	I _{NO(ON)} , I _{NC(ON)}	V_{COM} = Open, or V_{NC} or V_{NO} = 4.5 V, V_{COM} = Open,	Switch ON, See Figure 16	Full	5.5 V	-100		100	nA
COM		V_{NC} or $V_{NO} = 0$ to 5.5 V,	Switch OFF,	25°C		-1	0.1	1	
OFF leakage current	I _{COM(PWROFF)}	$V_{COM} = 5.5 \text{ V to } 0,$	See Figure 15	Full	0 V	-20		20	μA
		V _{NC} or V _{NO} = Open,		25°C		-20	2	20	
COM ON leakage current	I _{COM(ON)}	$V_{COM} = 1 \text{ V},$ or $V_{NC} \text{ or } V_{NO} = \text{Open},$ $V_{COM} = 4.5 \text{ V},$	Switch ON, See Figure 16	Full	5.5 V	-100		100	nA
Digital Control I) ⁽²⁾				Г		1	
Input logic high	V _{IH}			Full		2.4		5.5	V
Input logic low	V _{IL}			Full		0		0.8	V
Input leakage	I _{IH} , I _{IL}	$V_1 = 5.5 \text{ V or } 0$		25°C	5.5 V	-2		2	nA
current		-		Full		-100		100	

The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

Electrical Characteristics for 5-V Supply⁽¹⁾ (continued)

 V_{+} = 4.5 V to 5.5 V, T_{A} = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONI	DITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Dynamic					1				
				25°C	5 V	1	8	13	
Turn-on time	t _{ON}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 18	Full	4.5 V to 5.5 V	1		16.5	ns
				25°C	5 V	1	5	8	
Turn-off time	t _{OFF}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 18	Full	4.5 V to 5.5 V	1		8	ns
				25°C	5 V	1	5.5	13	
Break-before- make time	t _{BBM}	$V_{NC} = V_{NO} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 19	Full	4.5 V to 5.5 V	1		14	ns
Charge injection	$Q_{\mathbb{C}}$	$V_{GEN} = 0,$ $R_{GEN} = 0,$	$C_L = 1 \text{ nF},$ See Figure 23	25°C	5 V		-7		рС
NC, NO OFF capacitance	$C_{NC(OFF)}, \ C_{NO(OFF)}$	V _{NC} or V _{NO} = V ₊ or GND, Switch OFF,	See Figure 17	25°C	5 V		18		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V _{NC} or V _{NO} = V ₊ or GND, Switch ON,	See Figure 17	25°C	5 V		55		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 17	25°C	5 V		54.5		pF
Digital input capacitance	C _I	$V_I = V_+$ or GND,	See Figure 17	25°C	5 V		2		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 20	25°C	5 V		100		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 1 MHz,	Switch OFF, See Figure 21	25°C	5 V		-64		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, f = 1 MHz,	Switch ON, See Figure 22	25°C	5 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \ \Omega,$ $C_L = 50 \ pF,$	f = 20 Hz to 20 kHz, See Figure 24	25°C	5 V		0.004		%
Supply							-	-	-
Positive		V V 0ND	0 :: 1 0 !! 0 ==	25°C			10	50	
supply current	I ₊	$V_1 = V_+ \text{ or GND},$	Switch ON or OFF	Full	5.5 V			750	nA



Electrical Characteristics for 3.3-V Supply⁽¹⁾

 $V_{+} = 3 \text{ V}$ to 3.6 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CON	DITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch		1				1		I	
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V+	V
Peak ON resistance	r _{peak}	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 14	25°C Full	3 V		1.3	1.6	Ω
ON-state	_	V_{NO} or $V_{NC} = 2 V$,	Switch ON,	25°C	2.1/		1.2	1.5	
resistance	r _{on}	$I_{COM} = -100 \text{ mA},$	See Figure 14	Full	3 V			1.7	Ω
ON-state				25°C			0.1	0.15	
resistance match between channels	Δr_{on}	V_{NO} or $V_{NC} = 2 \text{ V}$, 0.8 V , $I_{COM} = -100 \text{ mA}$,	Switch ON, See Figure 14	Full	3 V		0.2		Ω
ON-state		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 14	25°C			0.15		
resistance flatness	r _{on(flat)}	V_{NO} or $V_{NC} = 2 \text{ V}, 0.8 \text{ V},$	Switch ON,	25°C	3 V				Ω
natriess		$I_{COM} = -100 \text{ mA},$	See Figure 14	Full					
		V_{NC} or $V_{NO} = 1 V$,		25°C		-20	2	20	
NC, NO OFF leakage current	I _{NO(OFF)} , I _{NC(OFF)}	$\begin{split} &V_{COM} = 1 \text{ V to 3 V,} \\ &\text{or} \\ &V_{NC} \text{ or } V_{NO} = 3 \text{ V,} \\ &V_{COM} = 1 \text{ V to 3 V,} \end{split}$	Switch OFF, See Figure 15	Full	3.6 V	-50		50	nA
Current	I _{NC(PWROFF)} ,	V_{NC} or $V_{NO} = 0$ to 3.6 V,	Switch OFF,	25°C	0.17	-1	0.2	1	
	I _{NO(PWROFF)}	$V_{COM} = 3.6 \text{ V to } 0,$	See Figure 15	Full	0 V	-15		15	μA
		V_{NC} or $V_{NO} = 1 V$,		25°C		-10	2	10	
NC, NO ON leakage current	I _{NO(ON)} , I _{NC(ON)}	$ \begin{aligned} & V_{COM} = Open, \\ & or \\ & V_{NC} \ or \ V_{NO} = 3 \ V, \\ & V_{COM} = Open, \end{aligned} $	Switch ON, See Figure 16	Full	3.6 V	-20		20	nA
COM		V_{NC} or $V_{NO} = 3.6 \text{ V to 0}$,	Switch OFF,	25°C		-1	0.2	1	
OFF leakage current	I _{COM(PWROFF)}	$V_{COM} = 0 \text{ to } 3.6 \text{ V},$	See Figure 15	Full	0 V	-15		15	μA
		V _{NC} or V _{NO} = Open,		25°C		-10	2	10	
COM ON leakage current	I _{COM(ON)}	$ \begin{aligned} &V_{COM} = 1 \ V, \\ ∨ \\ &V_{NC} \ or \ V_{NO} = Open, \\ &V_{COM} = 3 \ V, \end{aligned} $	Switch ON, See Figure 16	Full	3.6 V	-20		20	nA
Digital Control In	puts (IN1, IN2) ⁽²⁾)							
Input logic high	V _{IH}			Full		2		5.5	V
Input logic low	V _{IL}			Full		0		0.8	V
Input leakage	I _{IH} , I _{IL}	V _I = 5.5 V or 0		25°C	3.6 V	-2 20		2	nA
Input leakage current	I _{IH} , I _{IL}	V _I = 5.5 V or 0		25°C Full	3.6 V	-2 -20		20	ı

The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

Electrical Characteristics for 3.3-V Supply⁽¹⁾ (continued)

 $V_{+} = 3 \text{ V}$ to 3.6 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONI	DITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Dynamic									
		V - V	C = 25 pF	25°C	3.3 V	5	11	19	
Turn-on time	t _{ON}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 18	Full	3 V to 3.6 V	3		22	ns
		$V_{COM} = V_+,$	$C_L = 35 pF,$	25°C	3.3 V	1	5	9	
Turn-off time	t _{OFF}	$R_L = 50 \Omega,$	See Figure 18	Full	3 V to 3.6 V	1		9	ns
Break-before-		$V_{NC} = V_{NO} = V_{+}$	$C_1 = 35 pF,$	25°C	3.3 V	1	7	17	
make time	t _{BBM}	$R_{L} = 50 \Omega,$	See Figure 19	Full	3 V to 3.6 V	1		20	ns
Charge injection	Q _C	V _{GEN} = 0, R _{GEN} = 0,	C _L = 1 nF, See Figure 23	25°C	3.3 V		-4		рС
NC, NO OFF capacitance	$C_{NC(OFF)}, \ C_{NO(OFF)}$	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch OFF,	See Figure 17	25°C	3.3 V		18		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V _{NC} or V _{NO} = V ₊ or GND, Switch ON,	See Figure 17	25°C	3.3 V		56		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 17	25°C	3.3 V		56		pF
Digital input capacitance	C _I	$V_I = V_+ \text{ or GND},$	See Figure 17	25°C	3.3 V		2		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 20	25°C	3.3 V		100		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 1 MHz,	Switch OFF, See Figure 21	25°C	3.3 V		-64		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, f = 1 MHz,	Switch ON, See Figure 22	25°C	3.3 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \ \Omega,$ $C_L = 50 \ pF,$	f = 20 Hz to 20 kHz, See Figure 24	25°C	3.3 V		0.01		%
Supply									
Positive supply current	I ₊	$V_1 = V_+ \text{ or GND},$	Switch ON or OFF	25°C Full	3.6 V			25 150	nA

Product Folder Links: TS5A23159



Electrical Characteristics for 2.5-V Supply⁽¹⁾

 $V_{+} = 2.3 \text{ V}$ to 2.7 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST COND	ITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V ₊	V
Peak ON	_	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON,	25°C	2.3 V		1.8	2.5	Ω
resistance	r _{peak}	$I_{COM} = -8 \text{ mA},$	See Figure 14	Full	2.3 V			2.7	12
ON-state	_	V_{NO} or $V_{NC} = 1.8 \text{ V}$,	Switch ON,	25°C	2.3 V		1.5	2	Ω
resistance	r _{on}	$I_{COM} = -8 \text{ mA},$	See Figure 14	Full	2.3 V			2.4	
ON-state				25°C			0.15	0.2	
resistance match between channels	Δr _{on}	V_{NO} or V_{NC} = 1.8 V, 0.8 V, I_{COM} = -8 mA,	Switch ON, See Figure 14	Full	2.3 V			0.2	Ω
ON-state		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -8 \text{ mA},$	Switch ON, See Figure 14	25°C			0.6		
resistance flatness	r _{on(flat)}	V_{NO} or $V_{NC} = 0.8 \text{ V}$, 1.8 V,	Switch ON.	25°C	2.3 V		0.6	1	Ω
nauiess		$I_{COM} = -8 \text{ mA},$	See Figure 14	Full				1	
		V_{NC} or $V_{NO} = 0.5 \text{ V}$,		25°C		-20	2	20	
NC, NO OFF leakage current	I _{NO(OFF)} , I _{NC(OFF)}	$\begin{aligned} &V_{COM} = 0.5 \text{ V to } 2.3 \text{ V,} \\ &\text{or} \\ &V_{NC} \text{ or } V_{NO} = 2.2 \text{ V,} \\ &V_{COM} = 0.5 \text{ V to } 2.3 \text{ V,} \end{aligned}$	Switch OFF, See Figure 15	Full	2.3 V	-50		50	nA
darront	I _{NC(PWROFF)} ,	V_{NC} or $V_{NO} = 0$ to 2.7 V,	Switch OFF,	25°C	0 V	-1	0.1	1.0	
	I _{NO(PWROFF)}	$V_{COM} = 2.7 \text{ V to } 0,$	See Figure 15	Full	UV	-10		10	μA
		V_{NC} or $V_{NO} = 0.5 \text{ V}$,		25°C		-10	2	10	
NC, NO ON leakage current	I _{NO(ON)} , I _{NC(ON)}	$V_{COM} = Open,$ or V_{NC} or $V_{NO} = 2.2 V,$ $V_{COM} = Open,$	Switch ON, See Figure 16	Full	2.7 V	-20		20	nA
COM		V_{NC} or $V_{NO} = 2.7 \text{ V to 0}$,	Switch OFF,	25°C		-1	0.1	1	
OFF leakage current	I _{COM(PWROFF)}	$V_{COM} = 0 \text{ to } 2.7 \text{ V},$	See Figure 15	Full	0 V	-10		10	μΑ
		V_{NC} or V_{NO} = Open,		25°C		-10	2	10	
COM ON leakage current	I _{COM(ON)}	$\begin{aligned} &V_{COM} = 0.5 \text{ V,} \\ &\text{or} \\ &V_{NC} \text{ or } V_{NO} = \text{Open,} \\ &V_{COM} = 2.2 \text{ V,} \end{aligned}$	Switch ON, See Figure 16	Full	2.7 V	-20		20	nA
Digital Control In)		,	I	T			
Input logic high	V _{IH}			Full		1.8		5.5	V
Input logic low	V_{IL}			Full		0		0.6	V
Input leakage	I _{IH} , I _{IL}	V _I = 5.5 V or 0		25°C	2.7 V	-2		2	nA
current	יווי, יונ	V ₁ = 0.0 V 01 0		Full	Z.1 V	-20		20	11/7

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

⁽²⁾ All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

Electrical Characteristics for 2.5-V Supply⁽¹⁾ (Continued)

 $V_{+} = 2.3 \text{ V}$ to 2.7 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONI	DITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Dynamic								•	
		., .,	0 05 5	25°C	2.5 V	5	15	28	
Turn-on time	t _{ON}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 18	Full	2.3 V to 2.7 V	5		32	ns
		., .,	0 05 5	25°C	2.5 V	2	6	9	
Turn-off time	t _{OFF}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 18	Full	2.3 V to 2.7 V	2		10	ns
		., ., .,		25°C	2.5 V	1	10	27	
Break-before- make time	t _{BBM}	$V_{NC} = V_{NO} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 19	Full	2.3 V to 2.7 V	1		30	ns
Charge injection	$Q_{\mathbb{C}}$	V _{GEN} = 0, R _{GEN} = 0,	C _L = 1 nF, See Figure 23	25°C	2.5 V		-3		рС
NC, NO OFF capacitance	C _{NC(OFF)} , C _{NO(OFF)}	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch OFF,	See Figure 17	25°C	2.5 V		18.5		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch ON,	See Figure 17	25°C	2.5 V		56.5		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 17	25°C	2.5 V		56.5		pF
Digital input capacitance	Cı	$V_I = V_+ \text{ or GND},$	See Figure 17	25°C	2.5 V		2		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 20	25°C	2.5 V		100		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch OFF, See Figure 21	25°C	2.5 V		-64		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch ON, See Figure 22	25°C	2.5 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 24	25°C	2.5 V		0.02		%
Supply									
Positive supply	1	$V_1 = V_+ \text{ or GND},$	Switch ON or OFF	25°C	2.7 V		10	25	r. Λ
current	I ₊	v ₁ = v ₊ or GND,	SWILCH ON OF OFF	Full	2.7 V			100	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

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Electrical Characteristics for 1.8-V Supply⁽¹⁾

 $V_{+} = 1.65 \text{ V}$ to 1.95 V, $T_{A} = -40 ^{\circ}\text{C}$ to 85 $^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST COND	DITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch						•			
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V ₊	V
Peak ON resistance	r _{peak}	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -2 \text{ mA},$	Switch ON, See Figure 14	25°C Full	1.65 V		5	15	Ω
ON-state resistance	r _{on}	V_{NO} or $V_{NC} = 1.5 \text{ V}$, $I_{COM} = -2 \text{ mA}$,	Switch ON, See Figure 14	25°C Full	1.65 V		2	2.5 3.5	Ω
ON-state			_	25°C			0.15	0.4	
resistance match between channels	Δr _{on}	V_{NO} or $V_{NC} = 0.6 \text{ V}$, 1.5 V, $I_{COM} = -2 \text{ mA}$,	Switch ON, See Figure 14	Full	1.65 V		0.10	0.4	Ω
ON-state		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -2 \text{ mA},$	Switch ON, See Figure 14	25°C			5		
resistance flatness	r _{on(flat)}	V_{NO} or $V_{NC} = 0.6 \text{ V}$, 1.5 V,	Switch ON.	25°C	1.65 V		4.5		Ω
nau iess		$I_{COM} = -2 \text{ mA},$	See Figure 14	Full					
		V_{NC} or $V_{NO} = 0.3 \text{ V}$,		25°C		-20	2	20	
NC, NO OFF leakage	I _{NO(OFF)} , I _{NC(OFF)}	$V_{COM} = 0.3 \text{ V to } 1.65 \text{ V},$ or V_{NC} or $V_{NO} = 1.65 \text{ V},$ $V_{COM} = 0.3 \text{ V to } 1.65 \text{ V}$	Switch OFF, See Figure 15	Full	1.65 V	-50		50	nA
current	I _{NC(PWROFF)} ,	V_{NC} or $V_{NO} = 0$ to	Switch OFF,	25°C		-1	0.1	1	
	I _{NO(PWROFF)}	1.95 V, $V_{COM} = 1.95 V \text{ to } 0,$	See Figure 15	Full	0 V	- 5		5	μA
		V_{NC} or $V_{NO} = 0.3 \text{ V}$,		25°C		- 5	2	5	
NC, NO ON leakage current	I _{NO(ON)} , I _{NC(ON)}	V_{COM} = Open, or V_{NC} or V_{NO} = 1.65 V, V_{COM} = Open,	Switch ON, See Figure 16	Full	1.95 V	-20		20	nA
COM		V_{NC} or $V_{NO} = 1.95 \text{ V to } 0$,	Switch OFF,	25°C		-1	0.1	1	
OFF leakage current	I _{COM(PWROFF)}	$V_{COM} = 0 \text{ to } 1.95 \text{ V},$	See Figure 15	Full	0 V	-5		5	μA
- Carrotte		V _{NC} or V _{NO} = Open,		25°C		-10	2	10	
COM ON leakage current	I _{COM(ON)}	$V_{COM} = 0.3 \text{ V},$ or $V_{NC} \text{ or } V_{NO} = \text{Open},$ $V_{COM} = 1.65 \text{ V},$	Switch ON, See Figure 16	Full	1.95 V	-20		20	nA
Digital Control In	puts (IN1, IN2) ⁽²)							
Input logic high	V _{IH}			Full		1.5		5.5	V
Input logic low	V _{IL}			Full		0		0.6	V
Input leakage	1 1	V = 5 5 V or 0		25°C	1.95 V	-2		2	nΛ
current	I _{IH} , I _{IL}	$V_{I} = 5.5 \text{ V or } 0$		Full	1.95 V	-20		20	nA

 ⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
 (2) All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

Electrical Characteristics for 1.8-V Supply⁽¹⁾ (Continued)

 $V_{+} = 1.65 \text{ V}$ to 1.95 V, $T_{A} = -40 ^{\circ}\text{C}$ to 85 $^{\circ}\text{C}$ (unless otherwise noted)

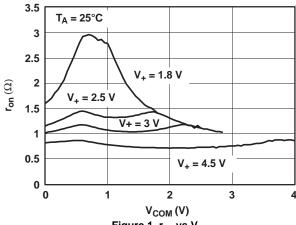
PARAMETER	SYMBOL	TEST CONI	DITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Dynamic									
		., .,	0 05 5	25°C	1.8 V	10	27.5	48.5	
Turn-on time	t _{ON}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 18	Full	1.65 V to 1.95 V	10		55	ns
		., .,	0 05 5	25°C	1.8 V	2	6.5	11	
Turn-off time	t _{OFF}	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 18	Full	1.65 V to 1.95 V	2		12	ns
				25°C	1.8 V	1	18	50	
Break-before- make time	t _{BBM}	$V_{NC} = V_{NO} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 19	Full	1.65 V to 1.95 V	1		55	ns
Charge injection	Q _C	V _{GEN} = 0, R _{GEN} = 0,	C _L = 1 nF, See Figure 23	25°C	1.8 V		2		рС
NC, NO OFF capacitance	C _{NC(OFF)} , C _{NO(OFF)}	V _{NC} or V _{NO} = V ₊ or GND, Switch OFF,	See Figure 17	25°C	1.8 V		18.5		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch ON,	See Figure 17	25°C	1.8 V		56.5		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 17	25°C	1.8 V		56.5		pF
Digital input capacitance	Cı	$V_I = V_+ \text{ or GND},$	See Figure 17	25°C	1.8 V		2		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 20	25°C	1.8 V		105		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, $f = 1 MHz$,	Switch OFF, See Figure 21	25°C	1.8 V		-64		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega,$ f = 1 MHz,	Switch ON, See Figure 22	25°C	1.8 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 24	25°C	1.8 V		0.06		%
Supply		*			•			,	
Positive supply		V V m CND	Cuitab ON as OFF	25°C	4.05.\/		10	25	A
current	I ₊	$V_I = V_+ \text{ or GND},$	Switch ON or OFF	Full	1.95 V			50	nA

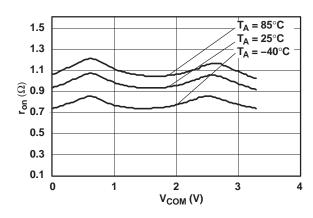
⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

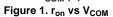
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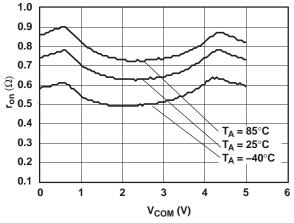
TYPICAL PERFORMANCE











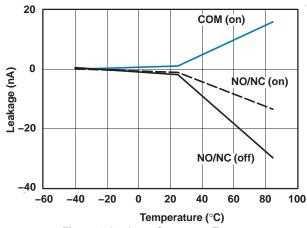
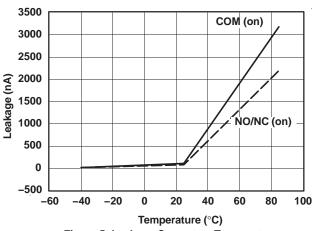


Figure 3. r_{on} vs V_{COM} ($V_{+} = 5 V$)

Figure 4. Leakage Current vs Temperature (V₊ = 3.3 V)



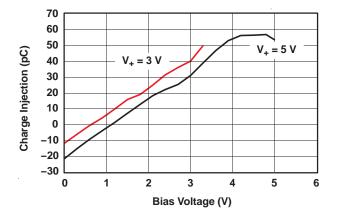


Figure 5. Leakage Current vs Temperature (V₊ = 5 V)

Figure 6. Charge Injection (Q_C) vs V_{COM}





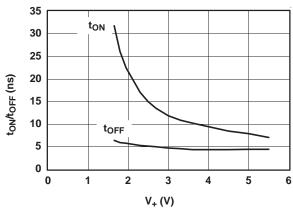


Figure 7. t_{ON} and t_{OFF} vs Supply Voltage

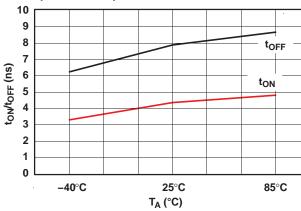


Figure 8. t_{ON} and t_{OFF} vs Temperature (5-V Supply)

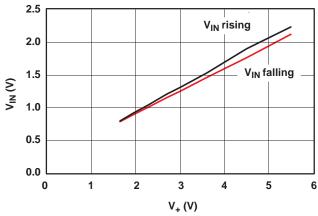


Figure 9. Logic-Level Threshold vs V₊

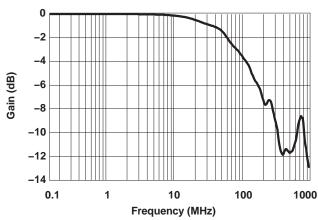


Figure 10. Bandwidth $(V_+ = 5 V)$

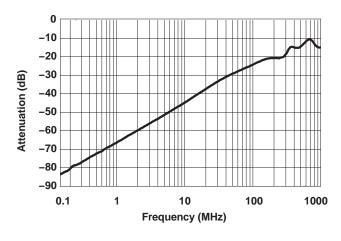


Figure 11. OFF Isolation vs Frequency

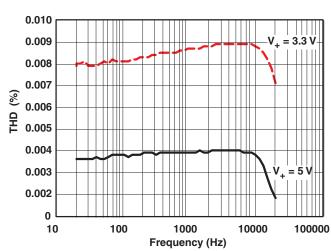


Figure 12. Total Harmonic Distortion vs Frequency



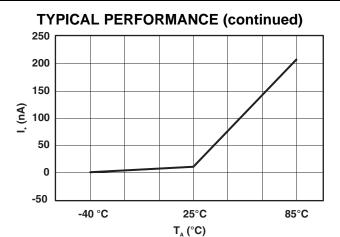


Figure 13. Power-Supply Current vs Temperature ($V_{+} = 5 \text{ V}$)

Table 1. PIN DESCRIPTION

PIN NO.	NAME	DESCRIPTION
1	IN1	Digital control to connect COM to NO or NC
2	NO1	Normally open
3	GND	Digital ground
4	NO2	Normally open
5	IN2	Digital control to connect COM to NO or NC
6	COM2	Common
7	NC2	Normally closed
8	V ₊	Power supply
9	NC1	Normally closed
10	COM1	Power supply

Table 2. PARAMETER DESCRIPTION

SYMBOL	DESCRIPTION
V _{COM}	Voltage at COM
V _{NC}	Voltage at NC
V _{NO}	Voltage at NO
r _{on}	Resistance between COM and NC or COM and NO ports when the channel is ON
r _{peak}	Peak on-state resistance over a specified voltage range
Δr _{on}	Difference of r _{on} between channels in a specific device
r _{on(flat)}	Difference between the maximum and minimum value of ron in a channel over the specified range of conditions
I _{NC(OFF)}	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state under worst-case input and output conditions
I _{NC(PWROFF)}	Leakage current measured at the NC port during the power-down condition, $V_{+} = 0$
I _{NO(OFF)}	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state under worst-case input and output conditions
I _{NO(PWROFF)}	Leakage current measured at the NO port during the power-down condition, $V_{+} = 0$
I _{NC(ON)}	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) open
I _{NO(ON)}	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) open
I _{COM(ON)}	Leakage current measured at the COM port, with the corresponding channel (COM to NO or COM to NC) in the ON state and the output (NC or NO) open
I _{COM(PWROFF)}	Leakage current measured at the COM port during the power-down condition, $V_{+} = 0$
V_{IH}	Minimum input voltage for logic high for the control input (IN)
V_{IL}	Maximum input voltage for logic low for the control input (IN)
V_{I}	Voltage at the control input (IN)
$I_{\rm IH},I_{\rm IL}$	Leakage current measured at the control input (IN)
t _{ON}	Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning ON.
t _{OFF}	Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, NC, or NO) signal when the switch is turning OFF.
t _{BBM}	Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state.
$Q_{\mathbb{C}}$	Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NO or COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, $Q_C = C_L \times \Delta V_{COM}$. C_L is the load capacitance and ΔV_{COM} is the change in analog output voltage.
$C_{NC(OFF)}$	Capacitance at the NC port when the corresponding channel (NC to COM) is OFF
$C_{NO(OFF)}$	Capacitance at the NO port when the corresponding channel (NO to COM) is OFF
C _{NC(ON)}	Capacitance at the NC port when the corresponding channel (NC to COM) is ON
C _{NO(ON)}	Capacitance at the NO port when the corresponding channel (NO to COM) is ON
$C_{COM(ON)}$	Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is ON
C _I	Capacitance of control input (IN)
O _{ISO}	OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state.
X _{TALK}	Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured in a specific frequency and in dB.
BW	Bandwidth of the switch. This is the frequency in which the gain of an ON channel is -3 dB below the DC gain.
THD	Total harmonic distortion is defined as the ratio of the root mean square (RMS) value of the second, third, and higher harmonics to the magnitude of fundamental harmonic.
I ₊	Static power-supply current with the control (IN) pin at V ₊ or GND



PARAMETER MEASUREMENT INFORMATION

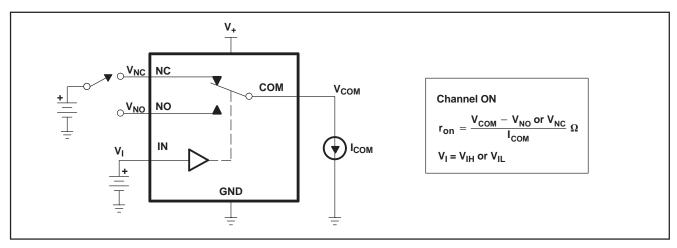


Figure 14. ON-State Resistance (ron)

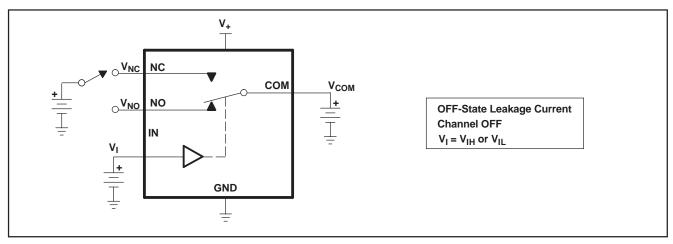


Figure 15. OFF-State Leakage Current (I_{NC(OFF)}, I_{NO(OFF)}, I_{NO(OFF)}, I_{NO(OFF)}, I_{COM(OFF)}, I_{COM(OFF)}, I_{COM(PWROFF)})

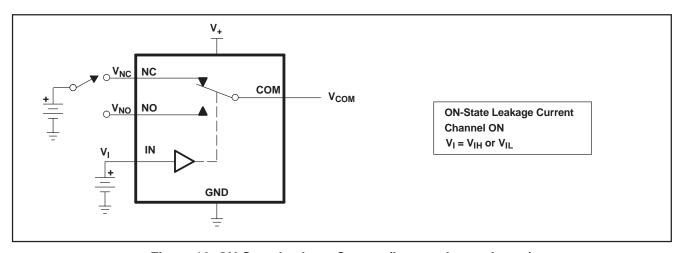


Figure 16. ON-State Leakage Current ($I_{COM(ON)}$, $I_{NC(ON)}$, $I_{NO(ON)}$)



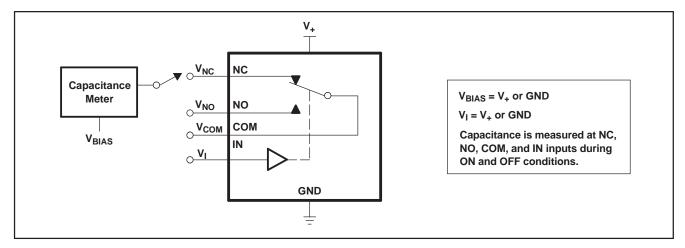
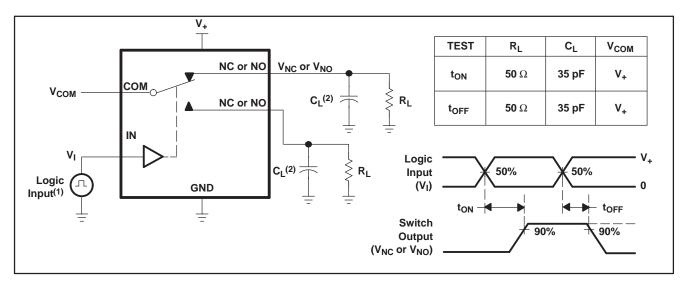


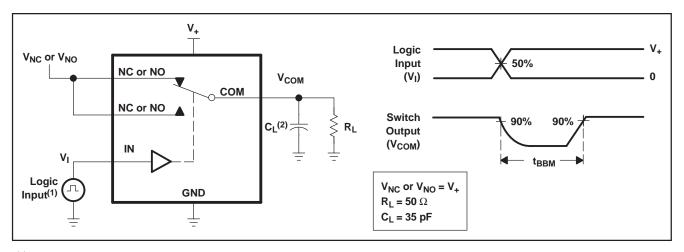
Figure 17. Capacitance (C_I, $C_{COM(ON)}$, $C_{NC(OFF)}$, $C_{NO(OFF)}$, $C_{NC(ON)}$, $C_{NO(ON)}$)



- (1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_r < 5 ns. t_f < 5 ns.
- $^{(2)}$ C_L includes probe and jig capacitance.

Figure 18. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})





- (1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_r < 5 ns, t_f < 5 ns.
- $^{(2)}$ C_L includes probe and jig capacitance.

Figure 19. Break-Before-Make Time (t_{BBM})

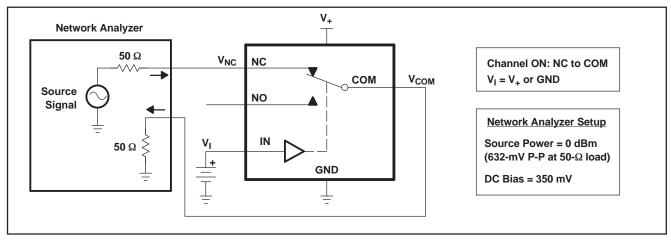


Figure 20. Bandwidth (BW)



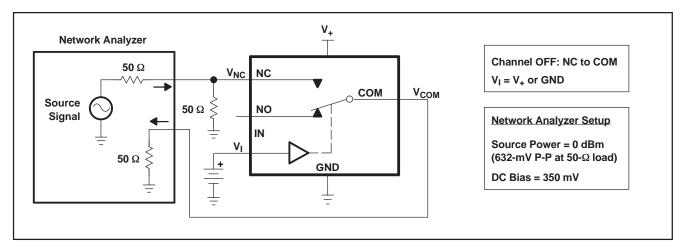


Figure 21. OFF Isolation (O_{ISO})

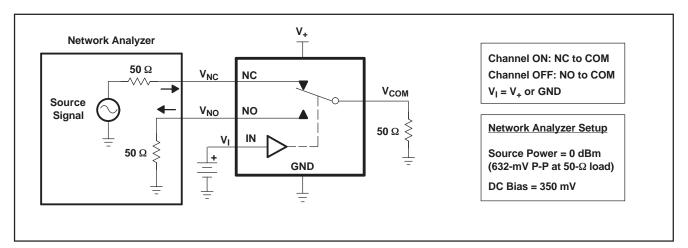
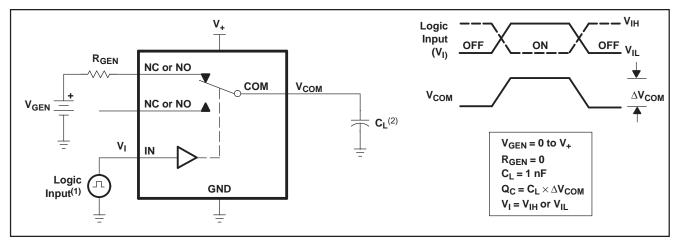


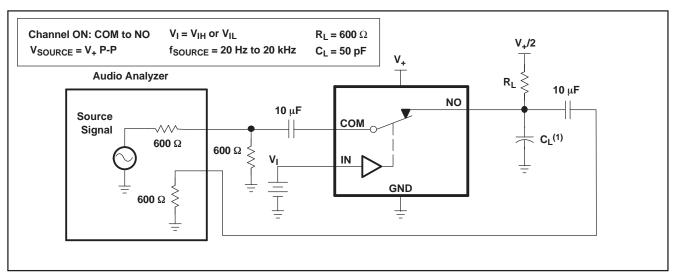
Figure 22. Crosstalk (X_{TALK})





- (1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_r < 5 ns, t_f < 5 ns.
- (2) C_L includes probe and jig capacitance.

Figure 23. Charge Injection (Q_C)



 $^{(1)}\,$ C_L includes probe and jig capacitance.

Figure 24. Total Harmonic Distortion (THD)



REVISION HISTORY

CI	Changes from Revision F (September 2010) to Revision G							
•	Aligned package description throughout datasheet.	1	1					
•	Removed Ordering Information Table.	1	1					





9-Aug-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	_		-	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)		(3)		(4/5)	
TS5A23159DGSR	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JER	Samples
TS5A23159DGSRE4	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JER	Samples
TS5A23159DGSRG4	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JER	Samples
TS5A23159DGST	ACTIVE	VSSOP	DGS	10	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JER	Samples
TS5A23159DGSTE4	ACTIVE	VSSOP	DGS	10	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JER	Samples
TS5A23159DGSTG4	ACTIVE	VSSOP	DGS	10	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	JER	Samples
TS5A23159RSER	ACTIVE	UQFN	RSE	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	(JE7 ~ JEO ~ JER)	Samples
TS5A23159RSERG4	ACTIVE	UQFN	RSE	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	(JE7 ~ JEO ~ JER)	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.



PACKAGE OPTION ADDENDUM

9-Aug-2013

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

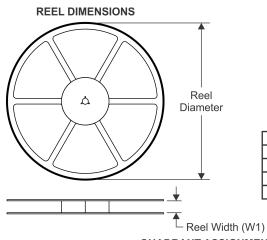
⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

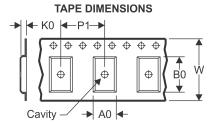
⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

PACKAGE MATERIALS INFORMATION

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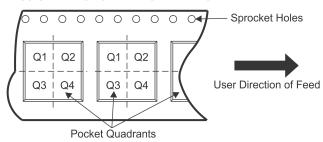
TAPE AND REEL INFORMATION





Α0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

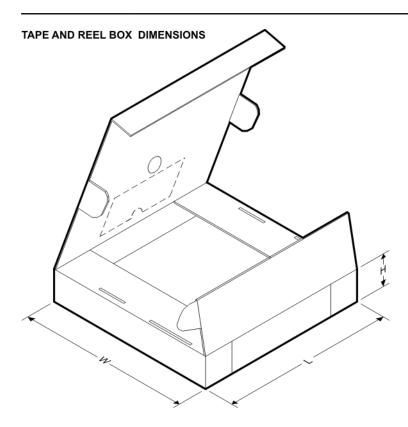


*All dimensions are nominal

All differsions are norminal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A23159DGSR	VSSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TS5A23159RSER	UQFN	RSE	10	3000	179.0	8.4	1.75	2.25	0.65	4.0	8.0	Q1
TS5A23159RSER	UQFN	RSE	10	3000	180.0	9.5	1.68	2.18	0.9	4.0	8.0	Q1
TS5A23159RSER	UQFN	RSE	10	3000	180.0	8.4	1.68	2.13	0.76	4.0	8.0	Q1

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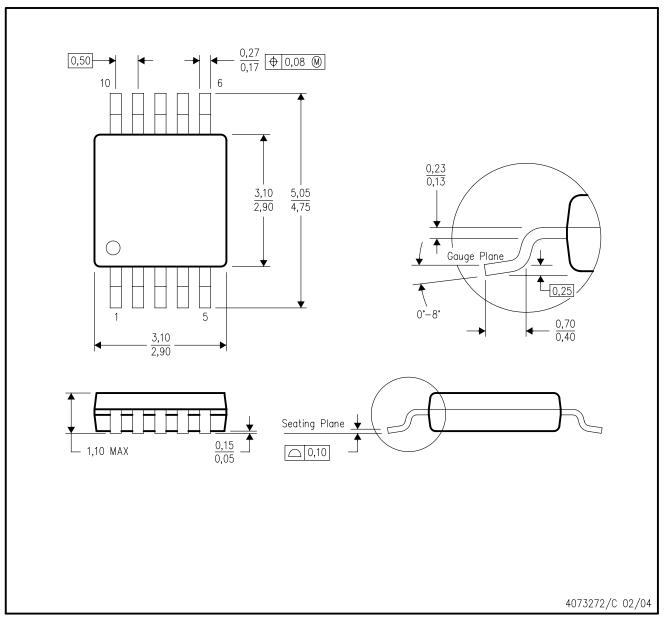


*All dimensions are nominal

7 till difficilities die fremman							
Device	Package Type	Package Type Package Drawing		SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A23159DGSR	VSSOP	DGS	10	2500	358.0	335.0	35.0
TS5A23159RSER	UQFN	RSE	10	3000	203.0	203.0	35.0
TS5A23159RSER	UQFN	RSE	10	3000	180.0	180.0	30.0
TS5A23159RSER	UQFN	RSE	10	3000	202.0	201.0	28.0

DGS (S-PDSO-G10)

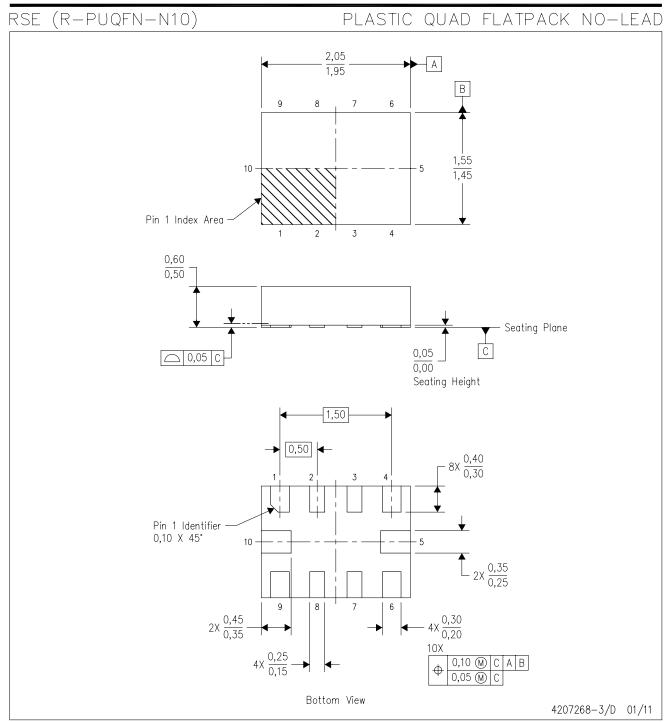
PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-187 variation BA.





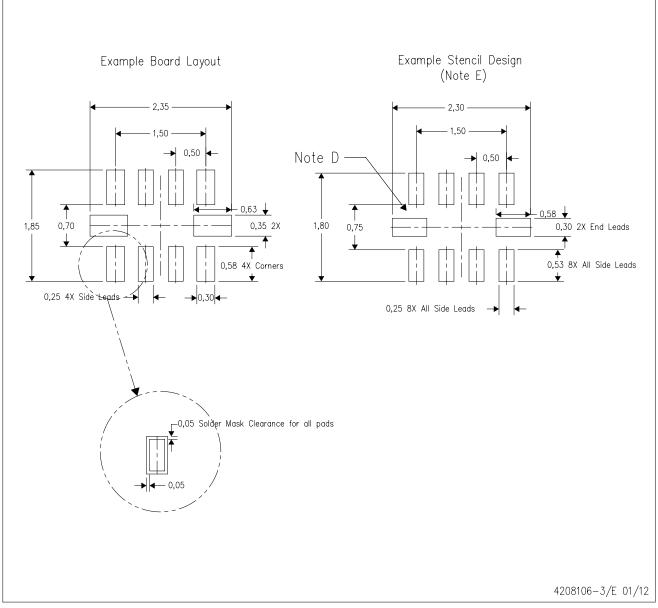
NOTES: All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
 C. QFN (Quad Flatpack No-Lead) package configuration.
 D. This package complies to JEDEC MO-288 variation UEFD.



RSE (R-PUQFN-N10)

PLASTIC QUAD FLATPACK NO-LEAD



- NOTES: A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.
 - E. Maximum stencil thickness 0,127 mm (5 mils). All linear dimensions are in millimeters.
 - F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 - G. Side aperture dimensions over-print land for acceptable area ratio > 0.66. Customer may reduce side aperture dimensions if stencil manufacturing process allows for sufficient release at smaller opening.



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